

# LH53B8500

CMOS 8M (1M × 8 / 512K × 16)  
Mask-Programmable ROM With Page Mode

## FEATURES

- 1,048,576 words × 8 bit organization (Byte mode)  
524,288 words × 16 bit organization (Word mode)
- Access time: 150 ns (MAX.)  
Page mode: 70 ns (MAX.)
- Addressable page: 4 words or 8 bytes
- Power consumption:  
Operating: 440 mW (MAX.)  
Standby: 550 μW (MAX.)
- Static operation
- TTL compatible I/O
- Three-state outputs
- Single +5 V power supply
- Packages:  
42-pin, 600-mil DIP  
44-pin, 600-mil SOP

## DESCRIPTION

The LH53B8500 is an 8M-bit mask-programmable ROM organized as 1,048,576 × 8 bits (Byte mode) or 524,288 × 16 bits (Word mode) with page mode operation. It is fabricated using silicon-gate CMOS process technology.

## PIN CONNECTIONS

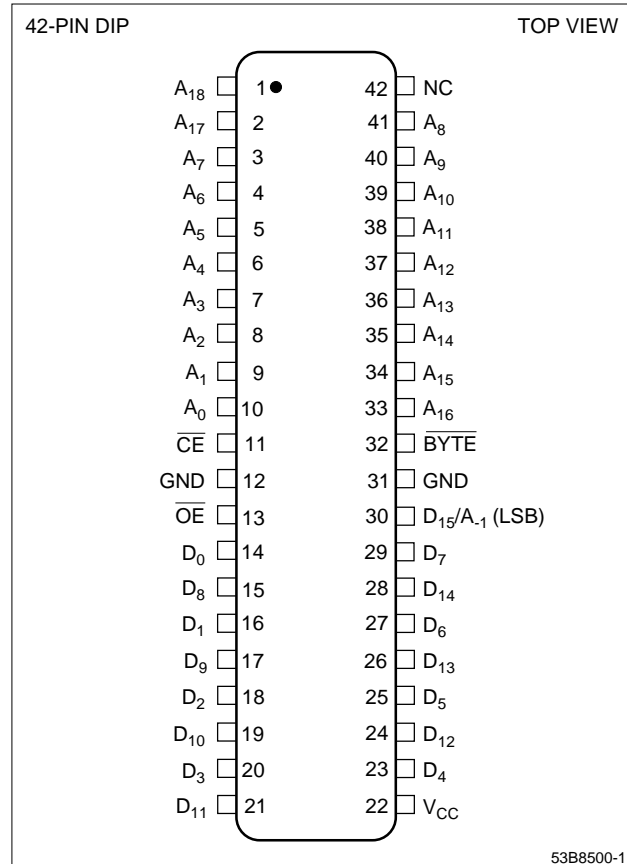
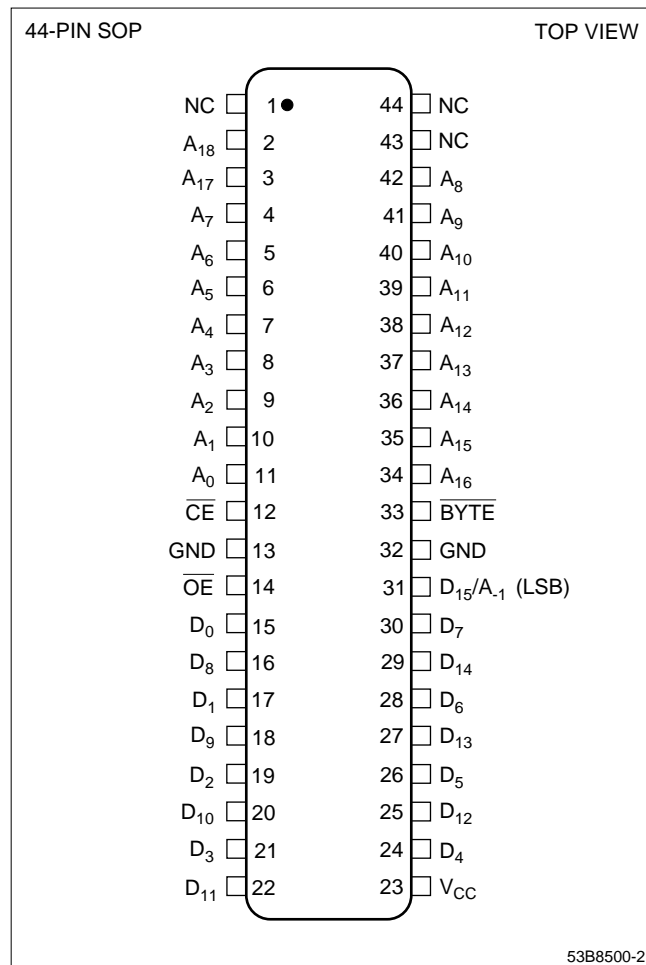


Figure 1. Pin Connections for DIP Package



**Figure 2. Pin Connections for SOP Package**

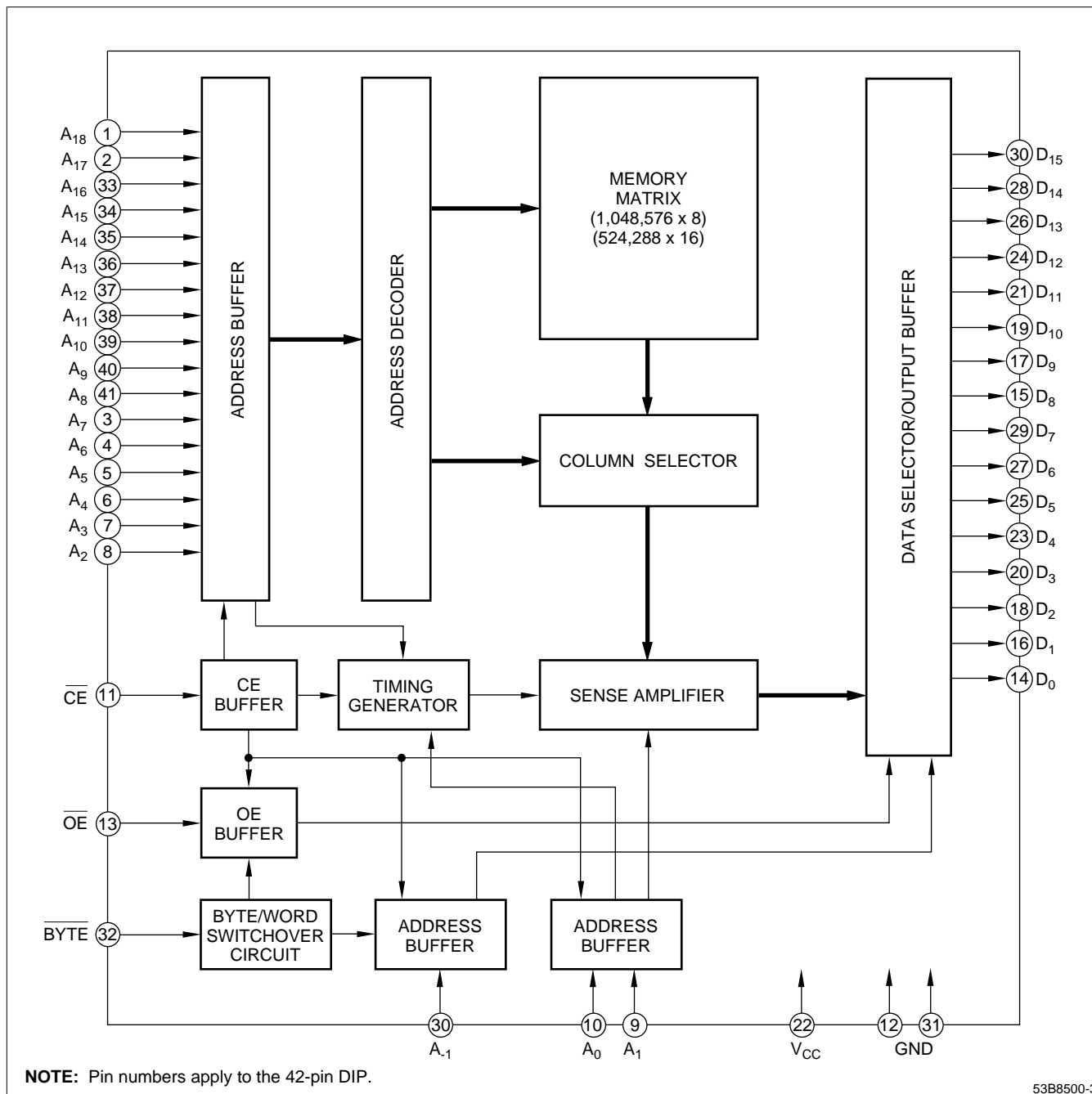


Figure 3. LH53B8500 Block Diagram

**PIN DESCRIPTION**

SIGNAL	PIN NAME	NOTE
A <sub>-1</sub> – A <sub>1</sub>	Address input (page mode operation)	1
A <sub>2</sub> – A <sub>18</sub>	Address input	
D <sub>0</sub> – D <sub>15</sub>	Data output	1
$\overline{\text{BYTE}}$	Byte/word mode switch	1

SIGNAL	PIN NAME	NOTE
$\overline{\text{CE}}$	Chip enable input	
$\overline{\text{OE}}$	Output enable input	
V <sub>CC</sub>	Power supply (+5 V)	
GND	Ground	

**NOTE:**

- The D<sub>15</sub>/A<sub>-1</sub> pin becomes LSB address input (A<sub>-1</sub>) when the  $\overline{\text{BYTE}}$  pin is set to be LOW in byte mode, and data output (D<sub>15</sub>) when set to be HIGH in word mode.

## TRUTH TABLE

$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{BYTE}}$	$A_{-1}$ ( $D_{15}$ )	DATA OUTPUT		ADDRESS INPUT		SUPPLY CURRENT
				$D_0 - D_7$	$D_8 - D_{15}$	LSB	MSB	
H	X	X	X	High-Z	High-Z	–	–	Standby
L	H	X	X	High-Z	High-Z	–	–	Operating
L	L	H	–	$D_0 - D_7$	$D_8 - D_{15}$	$A_0$	$A_{18}$	Operating
L	L	L	L	$D_0 - D_7$	High-Z	$A_{-1}$	$A_{18}$	Operating
L	L	L	H	$D_8 - D_{15}$	High-Z	$A_{-1}$	$A_{18}$	Operating

## NOTE:

X = H or L.

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply voltage	$V_{CC}$	–0.3 to +7.0	V
Input voltage	$V_{IN}$	–0.3 to $V_{CC} + 0.3$	V
Output voltage	$V_{OUT}$	–0.3 to $V_{CC} + 0.3$	V
Operating temperature	$T_{opr}$	0 to +70	°C
Storage temperature	$T_{stg}$	–65 to +150	°C

RECOMMENDED OPERATING CONDITIONS ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	$V_{CC}$	4.5	5.0	5.5	V

DC CHARACTERISTICS ( $V_{CC} = 5\text{ V} \pm 10\%$ ,  $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ )

PARAMETER	SYMBOL	CONDITIONS	MIN.	MAX.	UNIT	NOTE
Input 'Low' voltage	$V_{IL}$		–0.3	0.8	V	
Input 'High' voltage	$V_{IH}$		2.2	$V_{CC} + 0.3$	V	
Output 'Low' voltage	$V_{OL}$	$I_{OL} = 2.0\text{ mA}$		0.4	V	
Output 'High' voltage	$V_{OH}$	$I_{OH} = -400\text{ }\mu\text{A}$	2.4		V	
Input leakage current	$ I_{LI} $	$V_{IN} = 0\text{ V to }V_{CC}$		10	$\mu\text{A}$	
Output leakage current	$ I_{LO} $	$V_{OUT} = 0\text{ V to }V_{CC}$		10	$\mu\text{A}$	1
Operating current	$I_{CC1}$	$t_{RC} = 150\text{ ns}$		80	mA	2
	$I_{CC2}$	$t_{RC} = 1\text{ }\mu\text{s}$		60	mA	2
Standby current	$I_{SB1}$	$\overline{\text{CE}} = V_{IH}$		2	mA	
	$I_{SB2}$	$\overline{\text{CE}} = V_{CC} - 0.2\text{ V}$		100	$\mu\text{A}$	
Input capacitance	$C_{IN}$	$f = 1\text{ MHz}$		10	pF	
Output capacitance	$C_{OUT}$	$T_A = 25^\circ\text{C}$		10	pF	

## NOTES:

- $\overline{\text{CE}}/\overline{\text{OE}} = V_{IH}$
- $V_{IN} = V_{IH}$  or  $V_{IL}$ ,  $\overline{\text{CE}} = V_{IL}$ , outputs open

**AC CHARACTERISTICS ( $V_{CC} = 5\text{ V} \pm 10\%$ ,  $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ )**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Read cycle time	$t_{RC}$	150		ns	
Address access time	$t_{AA}$		150	ns	
Chip enable access time	$t_{ACE}$		150	ns	
Page address access time	$t_{APA}$		70	ns	
Output enable delay time	$t_{OE}$		70	ns	
Output hold time	$t_{OH}$	5		ns	
CE to output in High-Z	$t_{CHZ}$		60	ns	1
OE to output in High-Z	$t_{OHZ}$		40	ns	1

**NOTE:**

1. This is the time required for the output to become high-impedance.

**AC TEST CONDITIONS**

PARAMETER	RATING
Input voltage amplitude	0.4 V to 2.6 V
Input rise/fall time	10 ns
Input reference level	1.5 V
Output reference level	0.8 and 2.2 V
Output load condition	1TTL + 100 pF

**CAUTION**

To stabilize the power supply, it is recommended that a high-frequency bypass capacitor be connected between the  $V_{CC}$  pin and the GND pin.

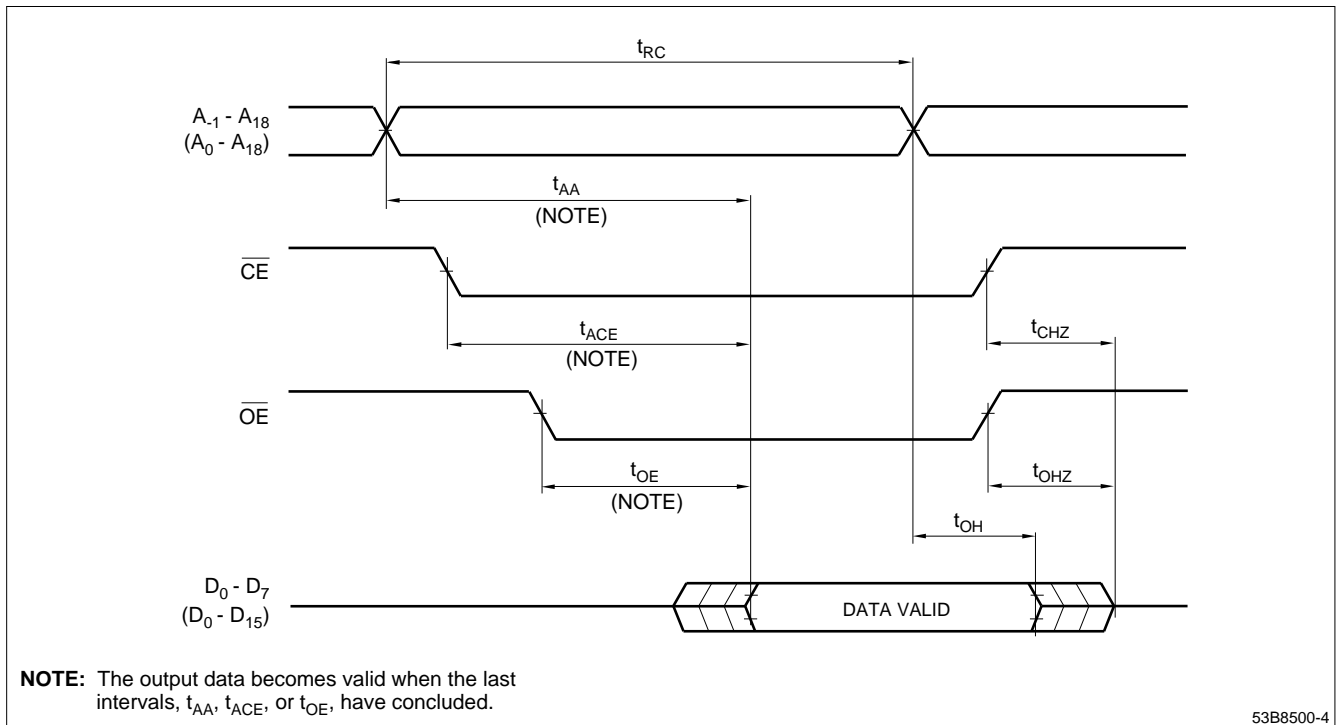


Figure 4. Read Cycle

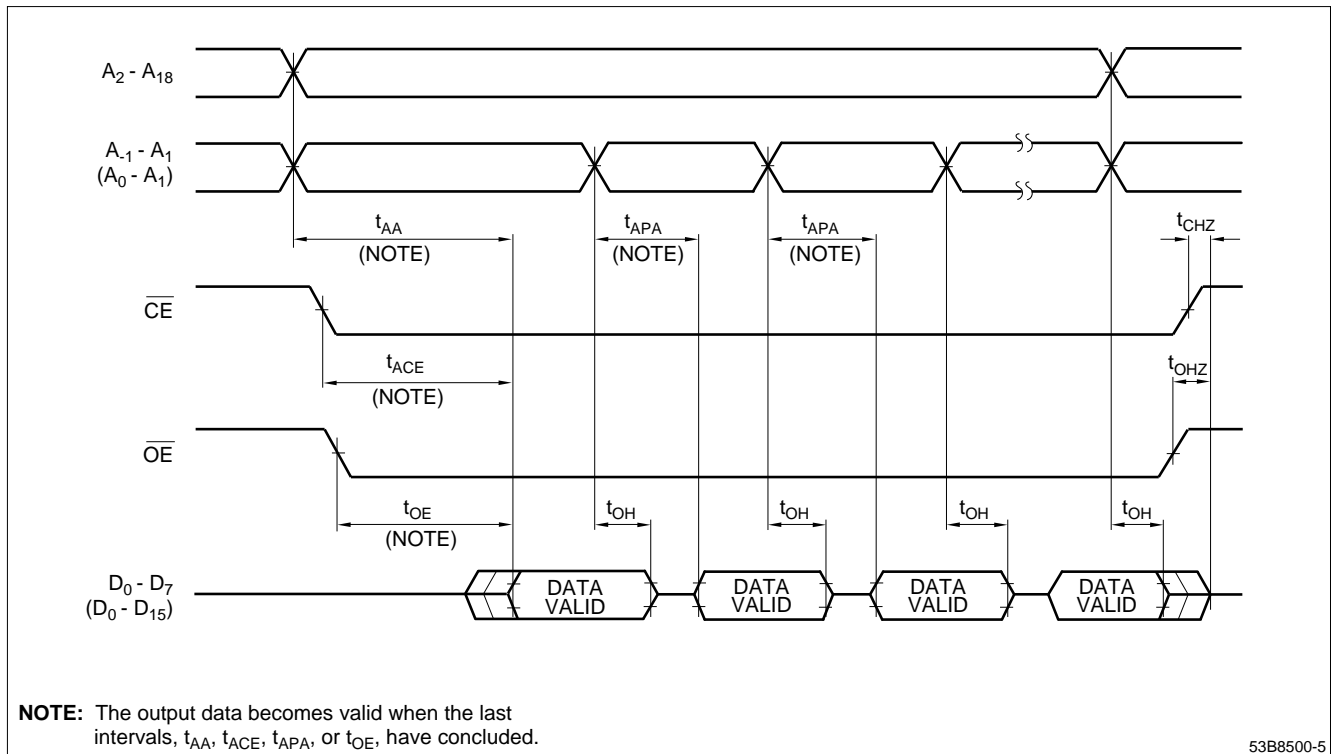
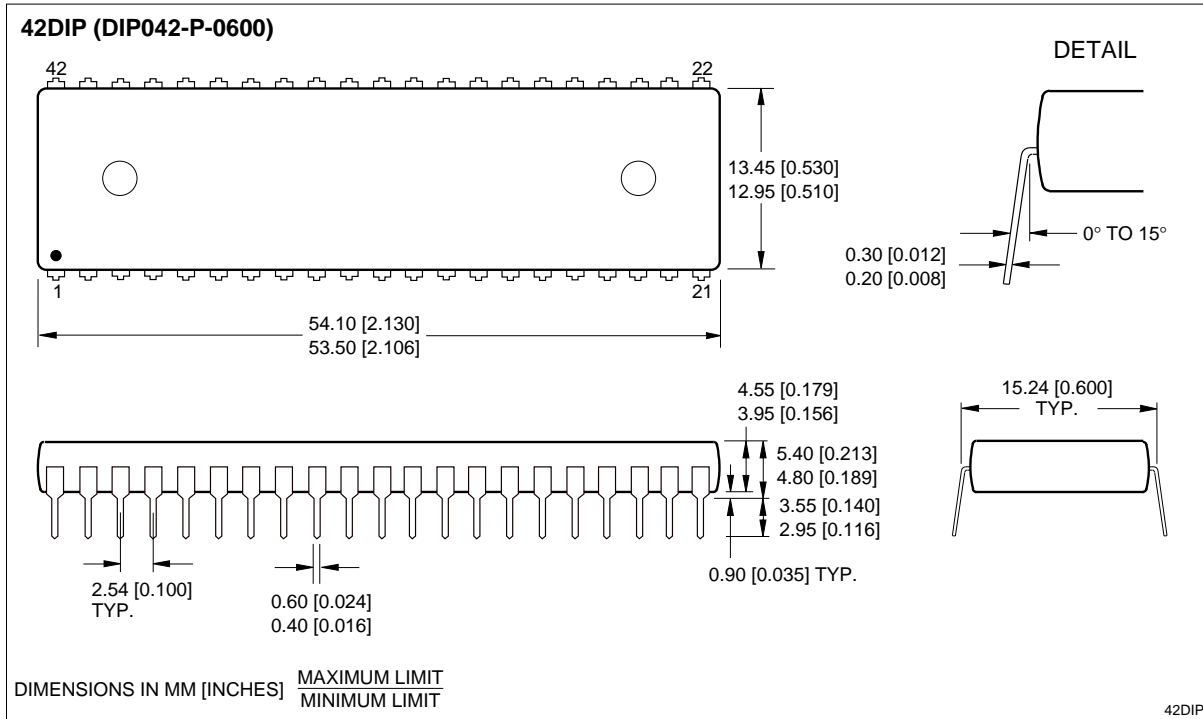
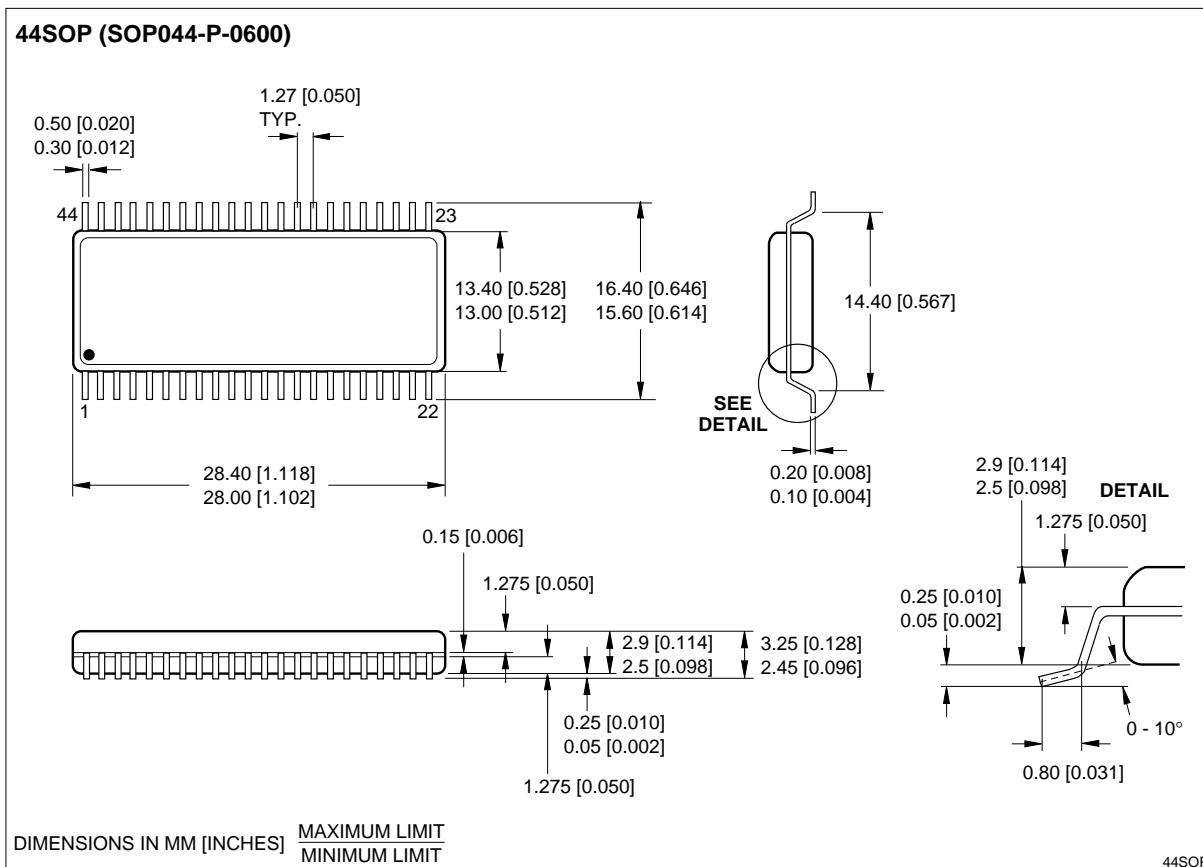


Figure 5. Page Mode Read Cycle

PACKAGE DIAGRAMS



42-pin, 600-mil DIP



44-pin, 600-mil SOP

**ORDERING INFORMATION**